

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

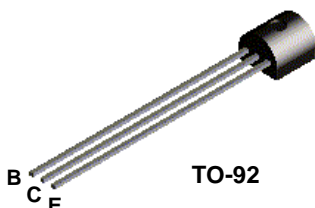
Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
 - Class Q Military
 - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
 - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

2N3663



NPN RF Transistor

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43. See PN918 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	12	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	3.0	V
I _C	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N3663	
P _D	Total Device Dissipation Derate above 25°C	350	mW
		2.8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	125	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	357	°C/W

NPN RF Transistor

(continued)

2N3663

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	12		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100 \mu\text{A}, I_C = 0$	3.0		V
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 15 \text{ V}, I_E = 0$		0.5	μA
I_{EBO}	Emitter-Cutoff Current	$V_{EB} = 2.0 \text{ V}, I_C = 0$		0.5	μA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$V_{CE} = 10 \text{ V}, I_C = 8.0 \text{ mA}$	20		
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SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}, f = 100 \text{ MHz}$	700	2100	MHz
C_{ob}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$	0.8	1.7	pF
$r_b'C_C$	Collector Base Time Constant	$I_C = 8.0 \text{ mA}, V_{CE} = 10 \text{ V}, f = 79.8 \text{ MHz}$		80	pS

FUNCTIONAL TEST

NF	Noise Figure	$I_C = 1.0 \text{ mA}, V_{CE} = 6.0 \text{ V}, f = 60 \text{ MHz}, R_g = 400 \Omega$		6.5	dB
G_{pe}	Amplifier Power Gain	$I_C = 6.0 \text{ mA}, V_{CE} = 12 \text{ V}, f = 200 \text{ MHz}$	1.5		dB

*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

TO-92 Tape and Reel Data

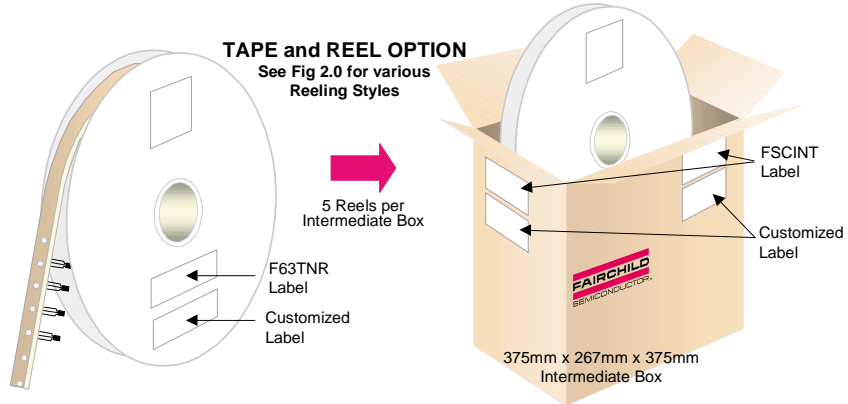


TO-92 Packaging Configuration: Figure 1.0

FSCINT Label sample



F63TNR Label sample



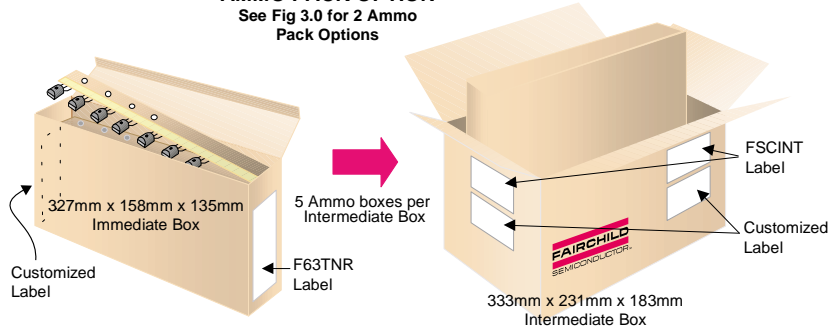
TO-92 TNR/AMMO PACKING INFORMATION

Packing	Style	Quantity	EOL code
Reel	A	2,000	D26Z
	E	2,000	D27Z
Ammo	M	2,000	D74Z
	P	2,000	D75Z

Unit weight = 0.22 gm
 Reel weight with components = 1.04 kg
 Ammo weight with components = 1.02 kg
 Max quantity per intermediate box = 10,000 units

AMMO PACK OPTION

See Fig 3.0 for 2 Ammo Pack Options

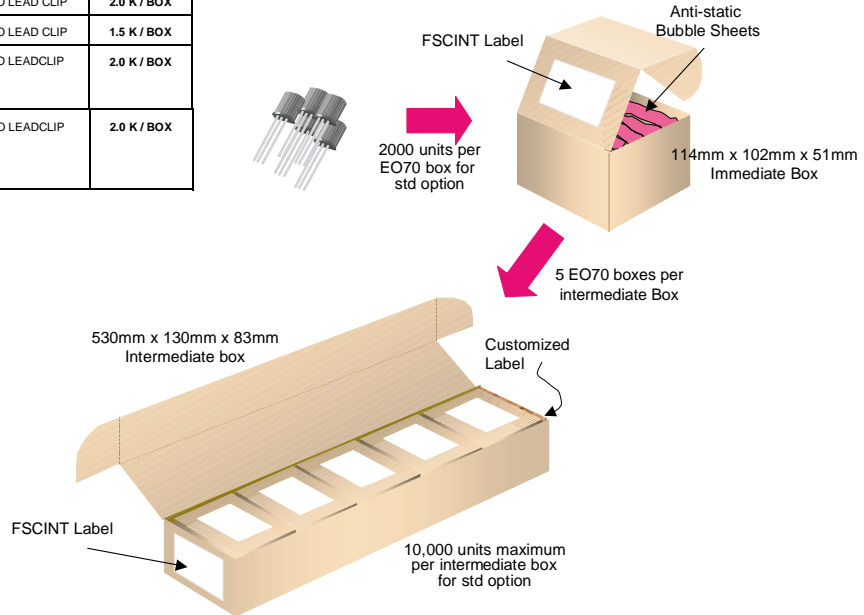


(TO-92) BULK PACKING INFORMATION

EOL CODE	DESCRIPTION	LEADCLIP DIMENSION	QUANTITY
J18Z	TO-18 OPTION STD	NO LEAD CLIP	2.0 K / BOX
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.5 K / BOX
NO EOL CODE	TO-92 STANDARD STRAIGHT FOR: PKG 92, 94 (NON PROELECTRON SERIES), 96	NO LEADCLIP	2.0 K / BOX
L34Z	TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98	NO LEADCLIP	2.0 K / BOX

BULK OPTION

See Bulk Packing Information table

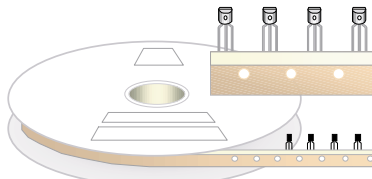


TO-92 Tape and Reel Data, continued

TO-92 Reeling Style

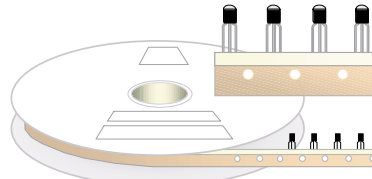
Configuration: Figure 2.0

Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

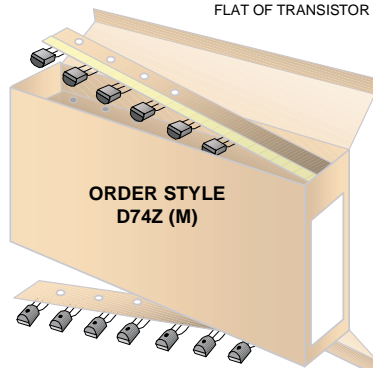


Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging

Configuration: Figure 3.0

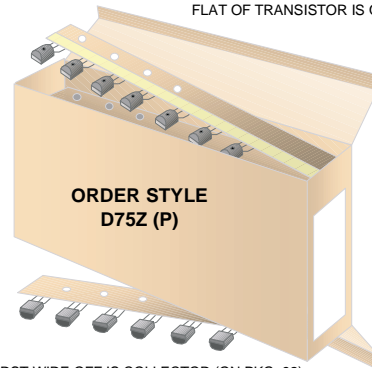
FIRST WIRE OFF IS COLLECTOR
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON TOP



ORDER STYLE
D74Z (M)

FIRST WIRE OFF IS EMITTER (ON PKG. 92)
ADHESIVE TAPE IS ON BOTTOM SIDE
FLAT OF TRANSISTOR IS ON BOTTOM

FIRST WIRE OFF IS EMITTER
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON BOTTOM

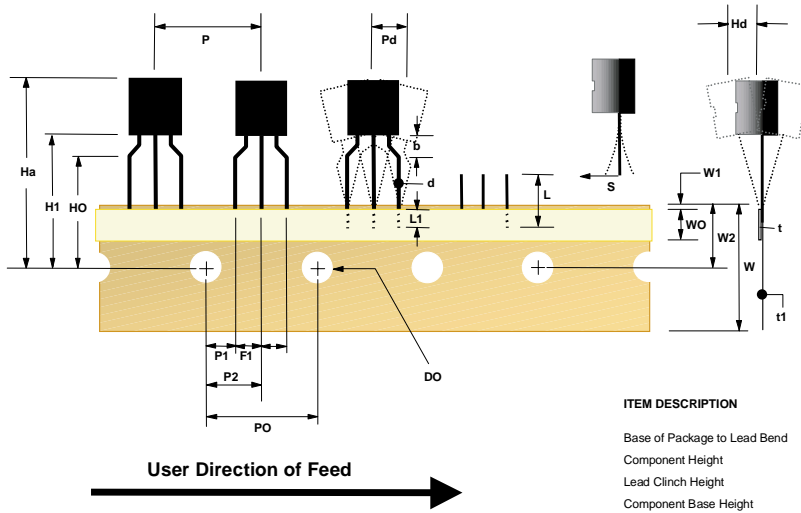


ORDER STYLE
D75Z (P)

FIRST WIRE OFF IS COLLECTOR (ON PKG. 92)
ADHESIVE TAPE IS ON BOTTOM SIDE
FLAT OF TRANSISTOR IS ON TOP

TO-92 Tape and Reel Data, continued

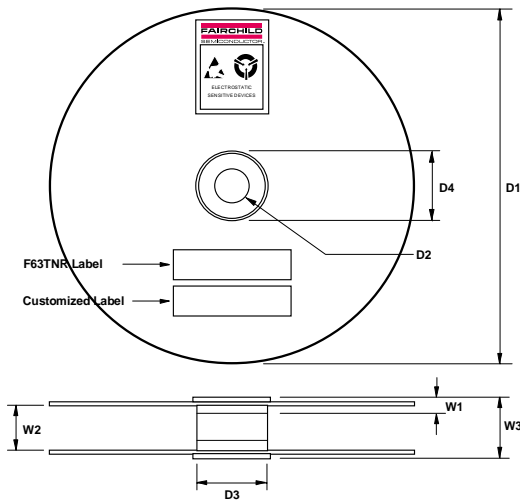
**TO-92 Tape and Reel Taping
Dimension Configuration: Figure 4.0**



ITEM DESCRIPTION	SYMBOL	DIMENSION
Base of Package to Lead Bend	b	0.098 (max)
Component Height	Ha	0.928 (+/- 0.025)
Lead Clinch Height	HO	0.630 (+/- 0.020)
Component Base Height	H1	0.748 (+/- 0.020)
Component Alignment (side/side)	Pd	0.040 (max)
Component Alignment (front/back)	Hd	0.031 (max)
Component Pitch	P	0.500 (+/- 0.020)
Feed Hole Pitch	PO	0.500 (+/- 0.008)
Hole Center to First Lead	P1	0.150 (+0.009, -0.010)
Hole Center to Component Center	P2	0.247 (+/- 0.007)
Lead Spread	F1/F2	0.104 (+/- 0.010)
Lead Thickness	d	0.018 (+0.002, -0.003)
Cut Lead Length	L	0.429 (max)
Taped Lead Length	L1	0.209 (+0.051, -0.052)
Taped Lead Thickness	t	0.032 (+/- 0.006)
Carrier Tape Thickness	t1	0.021 (+/- 0.006)
Carrier Tape Width	W	0.708 (+0.020, -0.019)
Hold - down Tape Width	WO	0.236 (+/- 0.012)
Hold - down Tape position	W1	0.035 (max)
Feed Hole Position	W2	0.360 (+/- 0.025)
Sprocket Hole Diameter	DO	0.157 (+0.008, -0.007)
Lead Spring Out	S	0.004 (max)

Note : All dimensions are in inches.

**TO-92 Reel
Configuration: Figure 5.0**



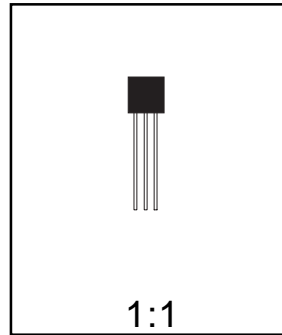
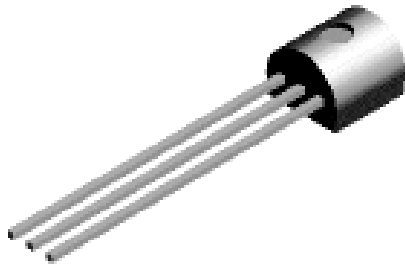
ITEM DESCRIPTION	SYMBOL	MINIMUM	MAXIMUM
Reel Diameter	D1	13.975	14.025
Arbor Hole Diameter (Standard)	D2	1.160	1.200
(Small Hole)	D2	0.650	0.700
Core Diameter	D3	3.100	3.300
Hub Recess Inner Diameter	D4	2.700	3.100
Hub Recess Depth	W1	0.370	0.570
Flange to Flange Inner Width	W2	1.630	1.690
Hub to Hub Center Width	W3		2.090

Note: All dimensions are in inches

TO-92 Package Dimensions



TO-92 (FS PKG Code 92, 94, 96)



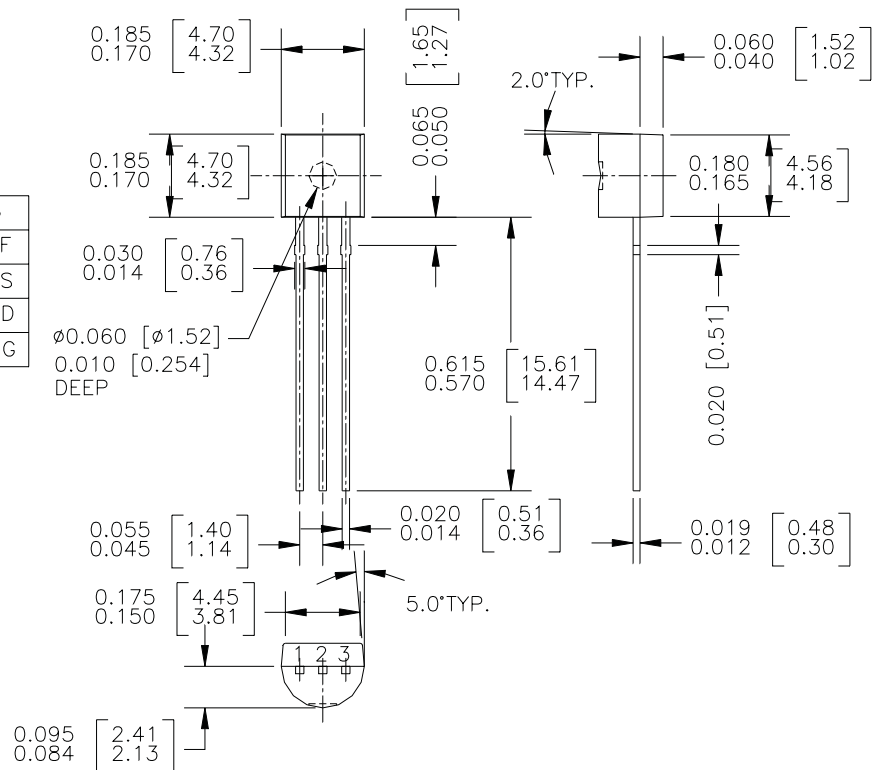
Scale 1:1 on letter size paper

Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977

TO-92 (92,94,96)

PIN	92		94		96	
	B	F	B	F	B	F
1	E	D	E	D	B	S
2	B	S	C	G	E	D
3	C	G	B	S	C	G



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CROSSVOLT™	HiSeC™	QT Optoelectronics™	VCX™
DOME™	ISOPLANAR™	Quiet Series™	
E ² CMOS™	MICROWIRE™	SILENT SWITCHER®	
EnSigna™	OPTOLOGIC™	SMART START™	
FACT™	OPTOPLANAR™	SuperSOT™-3	
FACT Quiet Series™	PACMAN™	SuperSOT™-6	
FAST®	POP™	SuperSOT™-8	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.